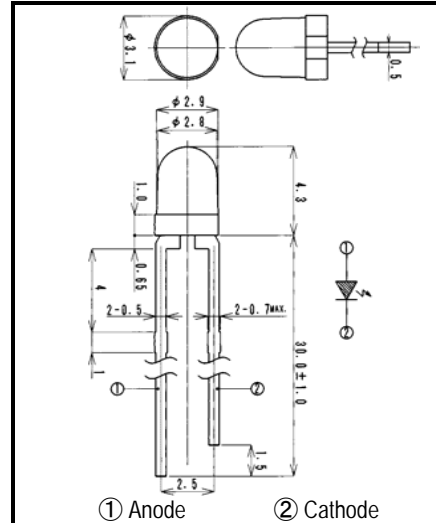
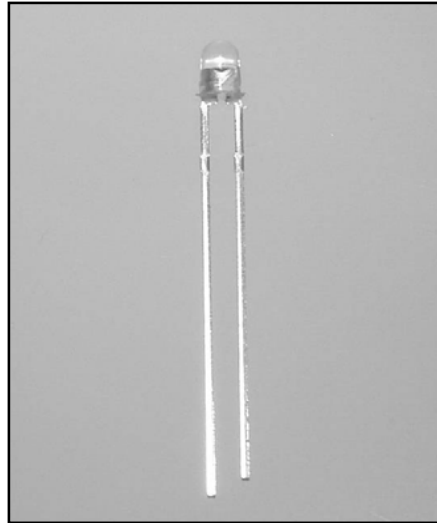


LSF850C1

Infrared Emitting Diode



- FEATURES**
- High-output Power
 - Compact
 - High Reliability
- APPLICATIONS**
- Optical Switches
 - Optical Sensors

1. ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

ITEM	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	60	mA
Forward Current (Pulse)*1	IFP	0.5	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	100	mW
Operating Temp.	ToPr	-20 TO 85	°C
Storage Temp.	Tstg	-30 TO 100	°C
Junction Temp.	Tj	100	°C
Lead Soldering Temp.*2	Tls	260	°C

*1:Tw=10uS,T=10mS

*2:Time 5 Sec max,Position:Up to 3mm from the body

2.ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25°C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=20mA		8.0		mW
Forward Voltage	VF	IF=20mA		1.4	1.9	V
Reverse Current	IR	VR=5V			100	μA
Peak Wavelength	λp	IF=20mA		850		nm
Spectral Line Half Width	Δλ	IF=20mA		30		nm
Half Intensity Beam Angle	θ	IF=20mA		±25		deg.

